TOSHIBA Field Effect Transistor with Built-in Schottky Barrier Diode Silicon N-Channel MOS Type (U-MOS V-H)

TPC8A03-H

High Efficiency DC-DC Converter Applications Notebook PC Applications Portable Equipment Applications

- Built-in schottky barrier diode
 Low forward voltage: V_{DSF} = -0.6 V (max)
- · High-speed switching
- Small gate charge: Q_{SW} = 8.4 nC (typ.)
- Low drain-source ON-resistance: $R_{DS (ON)} = 4.1 \text{ m}\Omega \text{ (typ.)}$
- High forward transfer admittance: |Y_{fs}| = 54 S (typ.)
- Low leakage current: I_{DSS} = 100 μA (max) (V_{DS} = 30 V)
- Enhancement mode: V_{th} = 1.3 to 2.3 V (V_{DS} = 10 V, I_D = 1 mA).

Absolute Maximum Ratings (Ta = 25°C)

| Characteristic | | Symbol | Rating | Unit | |
|--|----------------------------|----------------------|------------|----------|--|
| Drain-source voltage | | V _{DSS} < | 30 | y | |
| Drain-gate voltage ($R_{GS} = 20 \text{ k}\Omega$) | | V _{DGR} | 30 | / | |
| Gate-source voltage | | V _{GS} S | ±20 | V | |
| Drain current | DC (Note 1) | P | <u> </u> | A | |
| Drain current | Pulsed (Note 1) | ((I _{DP})) | 68 | | |
| Drain power dissipation | on (t = 10 s) (Note 2a) | PD | 1.9 W | | |
| Drain power dissipation (t = 10 s) (Note 2b) | | PD | (1.0/5) | W | |
| Single-pulse avalanche energy (Note 3) | | EAS | 188 | mJ | |
| Avalanche current | | I _{AR} | 17 | Α | |
| Repetitive avalanche energy (Tc = 25°C) (Note 4) | | EAR | 0.108 | mJ | |
| Channel temperature | | T _{ch} | 150 | °C | |
| Storage temperature range | | T _{stg} | –55 to 150 | °C | |
| | - 17 | | | | |

Note: For Notes 1 to 4, refer to the next page.

Unit: mm

0.595TYP 1.27

0.595TYP 1.27

0.595TYP 1.27

0.5±0.2

1, 2, 3 SOURCE GATE GATE
5, 6, 7, 8 DRAIN

JEDEC

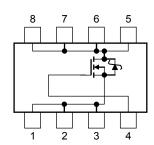
JEITA

TOSHIBA

2-6J1B

Weight: 0.085g (typ.)

Circuit Configuration



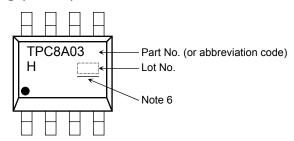
Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

This transistor is an electrostatic-sensitive device. Handle with care.

Thermal Characteristics

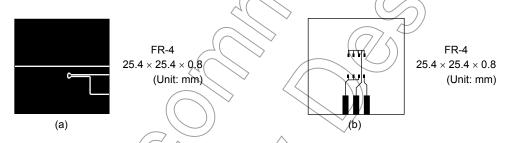
| Characteristic | Symbol | Max | Unit |
|--|------------------------|------|------|
| Thermal resistance, channel to ambient $(t = 10 \text{ s})$ (Note 2a) | R _{th (ch-a)} | 65.8 | °C/W |
| Thermal resistance, channel to ambient $(t=10\ s) \hspace{1.5cm} \text{(Note 2b)}$ | R _{th (ch-a)} | 125 | °C/W |

Marking (Note 5)



Note 1: Ensure that the channel temperature does not exceed 150 C.

Note 2: (a) Device mounted on a glass-epoxy board (b) Device mounted on a glass-epoxy board (b)



Note 3: $V_{DD} = 24 \text{ V}$, $T_{ch} = 25^{\circ}\text{C}$ (initial), L = 0.5 mH, $R_G = 25 \Omega$, $L_{R} = 17 \text{ A}$

Note 4: Repetitive rating: pulse width limited by maximum channel temperature

Note 5:

* Weekly code: (Three digits)

Week of manufacture
(01 for first week of year, continuing up to 52 or 53)

Year of manufacture

(The last digit of the calendar year)

Note 6: A line under a Lot No. identifies the indication of product Labels.

Not underlined: [[Pb]]/INCLUDES > MCV

Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product. The RoHS is the Directive 2002/95/EC of the European Parliament and of the Council of 27 January 2003 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

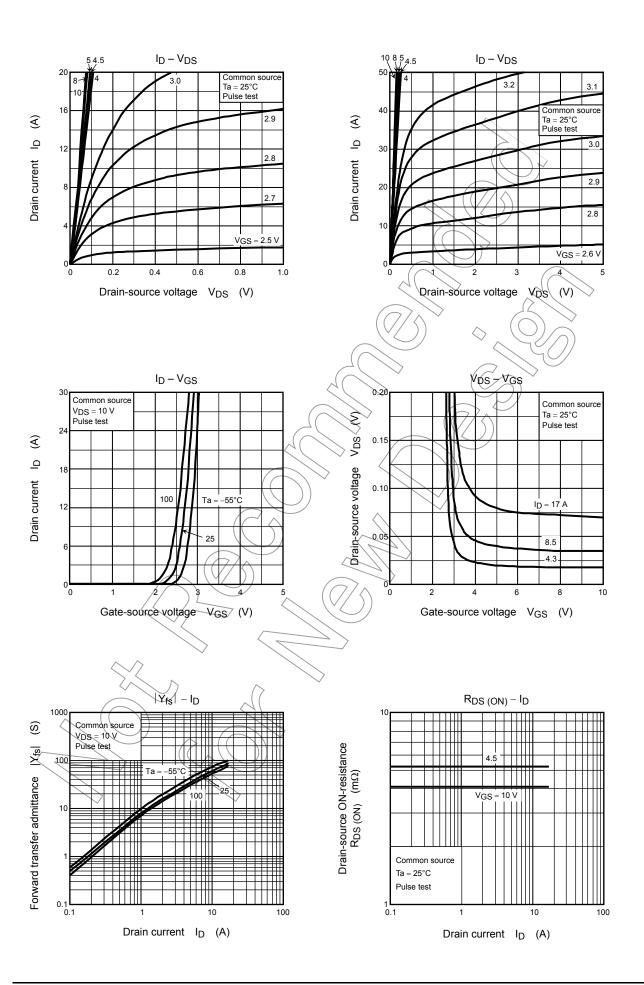
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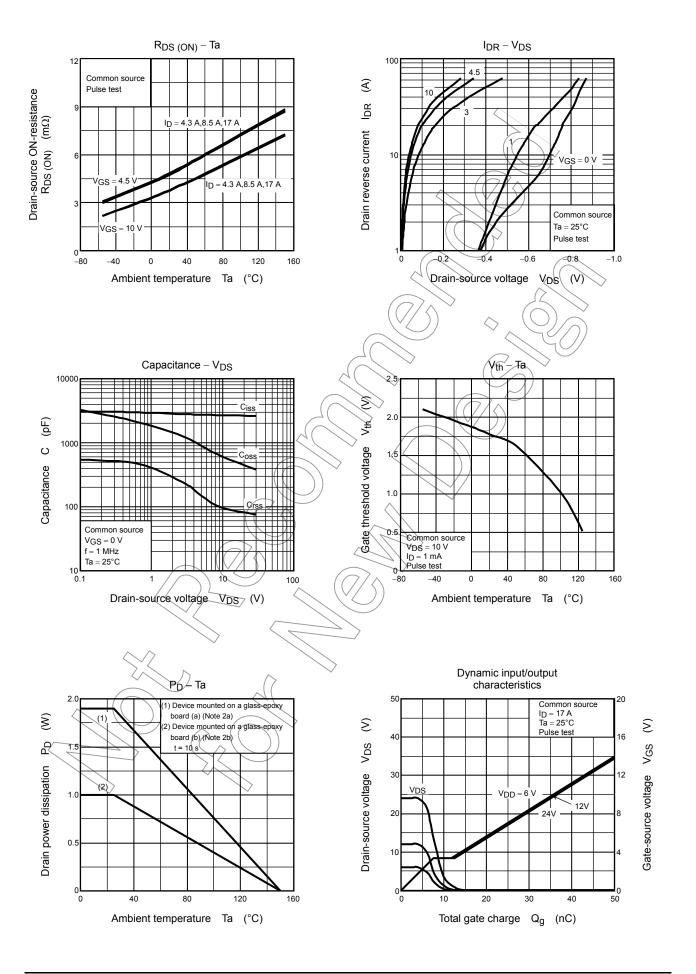
Electrical Characteristics (Ta = 25°C)

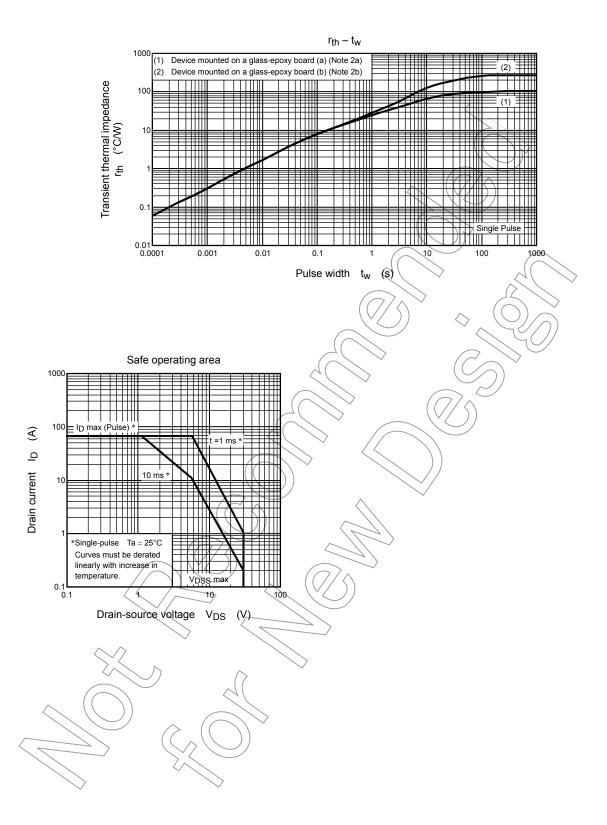
| Ch | aracteristic | Symbol | Test Condition | Min | Тур. | Max | Unit |
|--|---------------|-----------------------|---|---------------|------|--------------|------|
| Gate leakage cur | rent | I _{GSS} | $V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$ | _ | _ | ±100 | nA |
| Drain cut-off curre | ent | I _{DSS} | V _{DS} = 30 V, V _{GS} = 0 V | _ | _ | 100 | μА |
| Drain-source breakdown voltage | | V _{(BR) DSS} | $I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$ | 30 | _ | | V |
| | | V _{(BR) DSX} | $I_D = 10 \text{ mA}, V_{GS} = -20 \text{ V}$ | 15 | _ | | v |
| Gate threshold vo | oltage | V_{th} | $V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$ | 13 |) > | 2.3 | ٧ |
| Drain-source ON-resistance | | R _{DS} (ON) | $V_{GS} = 4.5 \text{ V}, I_D = 8.5 \text{ A}$ | | 5.1 | 7.0 | mΩ |
| | | | V _{GS} = 10 V, I _D = 8.5 A | \rightarrow | 4.1 | 5.6 | |
| Forward transfer | admittance | Y _{fs} | V _{DS} = 10 V, I _D = 8.5 A | 27 | 54 | | S |
| Input capacitance | | C _{iss} | | | 2640 | 3430 | |
| Reverse transfer | capacitance | C _{rss} | $V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$ | | 100 | 150 | pF |
| Output capacitan | ce | Coss | | | 610 | \checkmark | |
| Gate resistance | | rg | V _{DS} = 10 V, V _{GS} = 0 V, f = 5 MHz | - (| 1.0 | > 1.5 | Ω |
| Switching time | Rise time | t _r | 10V T ID = 8.5 A | 7 | 3.6 |) _ | |
| | Turn-on time | t _{on} | V _{GS} 10 V I _D = 8.5 A V _{OUT} | \(\int\) | 11.0 | | ns |
| | Fall time | t _f | 4. w w o & C | | 7.2 | — | 113 |
| | Turn-off time | t _{off} | Duty ≤ 1%, t _W =10 μs | _ | 42 | _ | |
| Total gate charge (gate-source plus gate-drain) | | Qg) | $V_{DD} \approx 24 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 17 \text{ A}$ | | 36 | | |
| | | | $V_{DD} \approx 24 \text{ V}, V_{GS} = 5 \text{ V}, V_{D} \neq 17 \text{ A}$ | _ | 19 | _ | |
| Gate-source char | rge 1 / | Qgs ₁ | | _ | 7.6 | _ | nC |
| Gate-drain ("Miller") charge | | Q_{gd} | $V_{DD} \approx 24 \text{ V} \text{ V}_{GS} = 10 \text{ V}, I_D = 17 \text{ A}$ | _ | 5.0 | _ | |
| Gate switch charge | | Q _{SW} | | _ | 8.4 | _ | |

Source-Drain Ratings and Characteristics (Ta = 25°C)

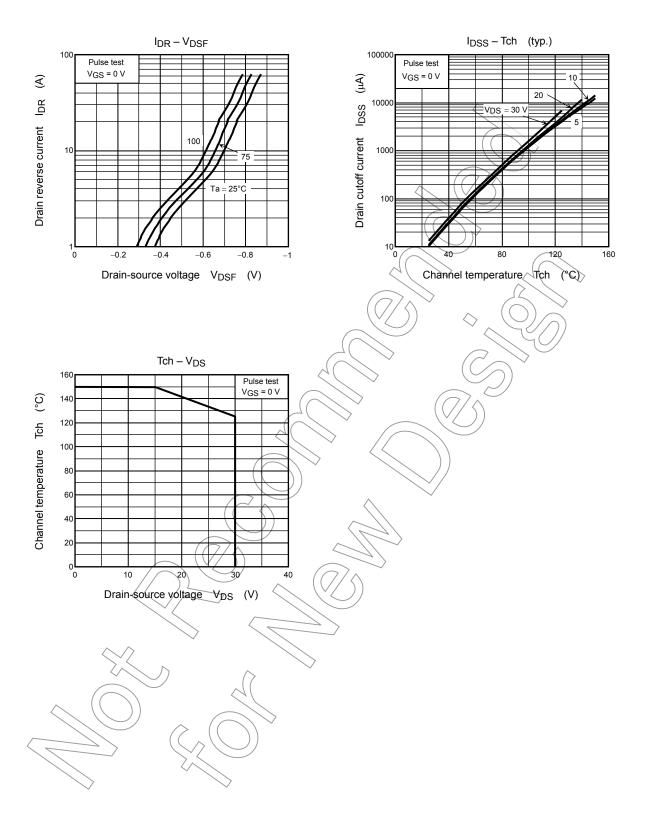
| Characteristic | Symbol | Test Condition | Min | Тур. | Max | Unit |
|--------------------------------------|------------------|---|-----|-------|-------|------|
| Drain reverse current Pulse (Note 1) | I _{DRP} | <u> </u> | _ | _ | 68 | Α |
| Equard voltage (diode) | | I _{DR} = 1 A, V _{GS} = 0 V | _ | - 0.4 | - 0.6 | V |
| Forward voltage (diode) | VDSF | I _{DR} = 17 A, V _{GS} = 0 V | _ | _ | - 1.2 | V |







6 2010-01-19



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